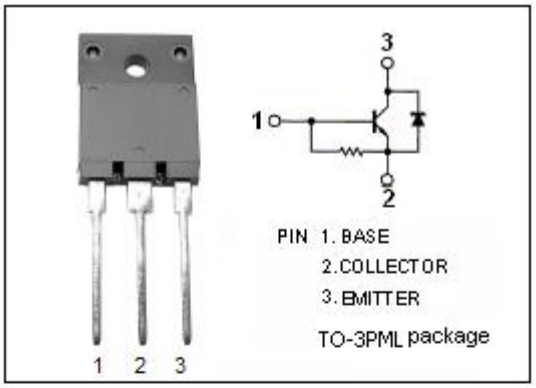
isc Silicon NPN Power Transistor 2SC4927



DESCRIPTION

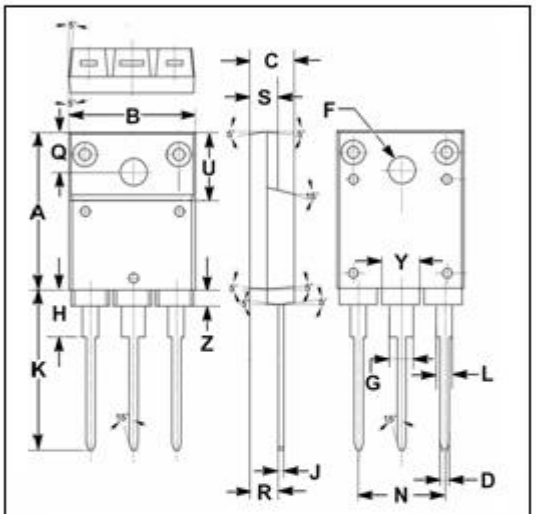
- High Breakdown Voltage-
  : V_{CES}= 1500V(Min)
- Built-in damper diode type
- Isolated package
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- TV/character display horizontal deflection output applications

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CES}	Collector-Emitter Voltage	1500	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	8	A
I_{CP}	Collector Current-Peak	9	A
P_C	Collector Power Dissipation @ T_C=25℃	50	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃
I_D	C-E Diode Forward Current	8	A



DIM	mm MIN	MAX
A	19.90	20.10
B	15.90	16.10
C	5.50	5.70
D	0.90	1.10
F	3.30	3.50
G	2.90	3.10
H	5.90	6.10
J	0.595	0.605
K	22.30	22.50
L	1.90	2.10
N	10.80	11.00
Q	4.90	5.10
R	3.75	3.95
S	3.20	3.40
U	9.90	10.10
Y	4.70	4.90
Z	1.90	2.10

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 500mA; I_C= 0	6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 6A; I_B= 1.2A			5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 6A; I_B= 1.2A			1.5	V
I_{CES}	Collector Cutoff Current	V_{CE}= 1500V ; R_{BE}= 0			500	μA
h_{FE}	DC current gain	I_C= 1A ; V_{CE}= 5V			25	
V_{ECF}	C-E Diode Forward Voltage	I_F=8A			2.0	V
Switching times						
t_f	Fall Time	I_C= 6A , I_{B1}= 1.2A; I_{B2}= -2.4A R_L= 33.3Ω ; f=31.5KHz			0.5	μs